

MOSFET N-Channel 60V MOSFET

Manufacturers	Infineon Technologies Corporation
Package/Case	PG-TO263-7-3
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPB180N06S4-H1 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

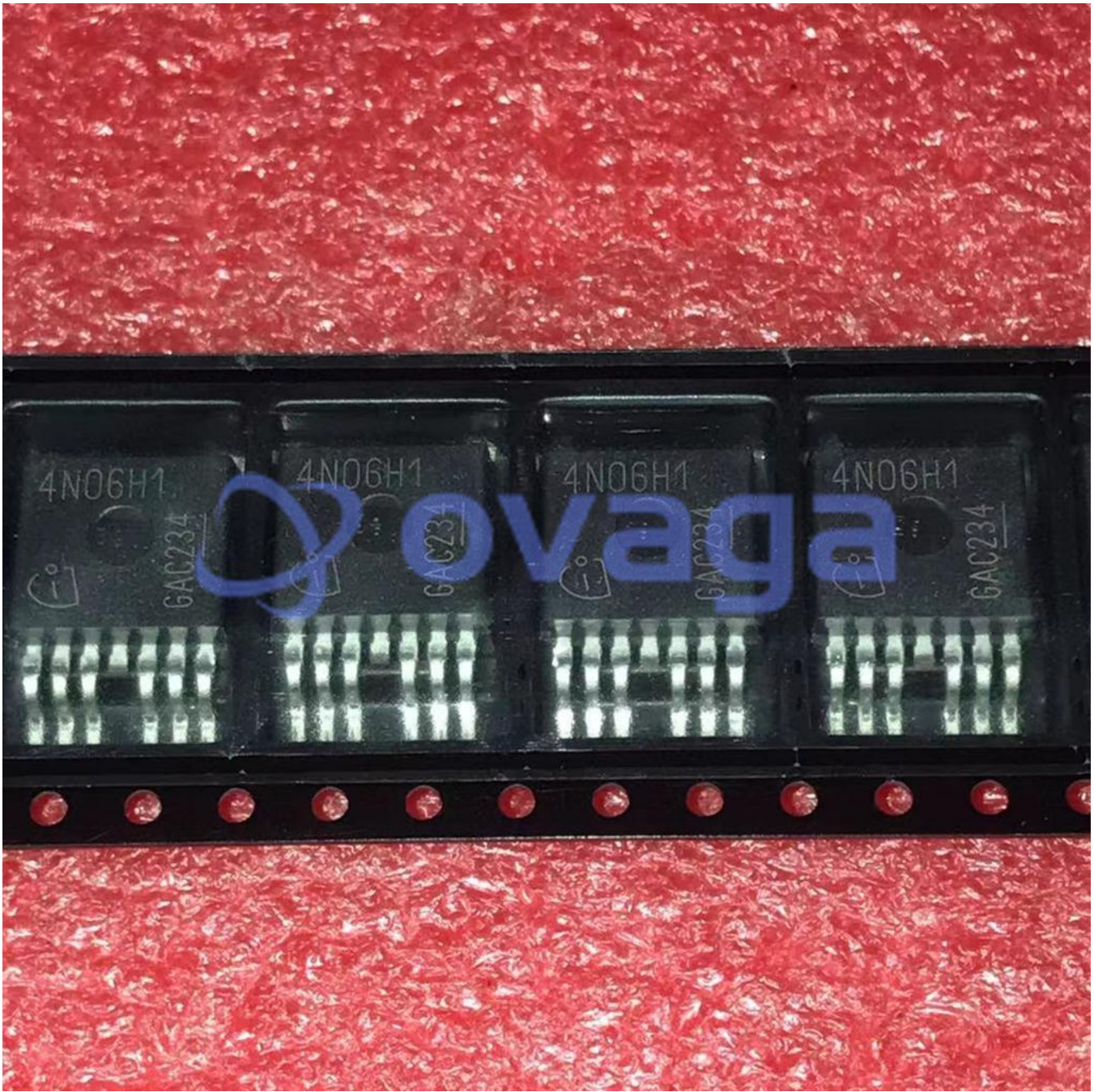
IPB180N06S4-H1 is a power MOSFET (Metal Oxide Semiconductor Field Effect Transistor) made by Infineon Technologies. It is designed to handle high currents and high voltages in power electronics applications.

Features

- Drain-Source Voltage (V_{ds}) of 60V
- Continuous Drain Current (I_d) of 180A
- Low On-Resistance ($R_{ds(on)}$) of 4.4m Ω
- Fast switching speed
- Avalanche rated

Application

- Power supplies
- DC-DC converters
- Motor control
- Solar inverters
- Uninterruptible Power Supplies (UPS)
- Battery management systems





Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
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[IPD25N06S4L-30](#)

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PG-TO252-3



[IPD180N10N3G](#)

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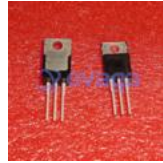
[IPP60R074C6](#)

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[IPP120P04P4L-03](#)

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